

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
100V	14mΩ @ V <sub>GS</sub> = 10V	59A
	20mΩ @ V <sub>GS</sub> = 6V	50A

## Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

## Applications

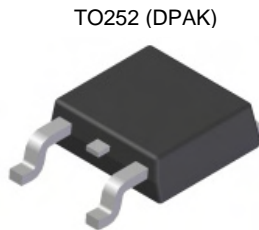
- Power Management Functions
- DC-DC Converters
- Backlighting

## Features

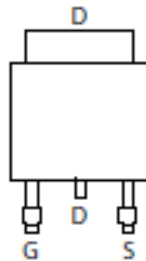
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> – Minimizes Power Losses
- Low Q<sub>g</sub> – Minimizes Switching Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.** <https://www.diodes.com/quality/product-definitions/>

## Mechanical Data

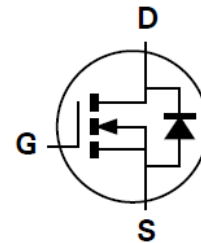
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓢ3
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



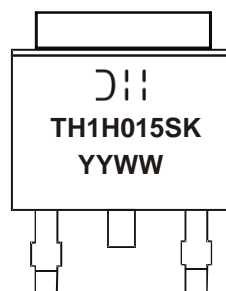
Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH10H015SK3-13	TO252 (DPAK)	2500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



☺|| = Manufacturer's Marking  
 TH1H015SK = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 21 = 2021)  
 WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	100	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>C</sub> = +25°C	59
		T <sub>C</sub> = +100°C	42
Pulsed Drain Current (10µs Pulse, T <sub>C</sub> = +25°C, Package Limited)	I <sub>DM</sub>	235	A
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	2.7	A
Pulsed Body Diode Forward Current (10µs Pulse, T <sub>C</sub> = +25°C, Package Limited)	I <sub>SM</sub>	235	A
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	15.8	A
Avalanche Energy, L = 0.1mH	E <sub>AS</sub>	12.5	mJ
Avalanche Current, L = 3mH (Note 8)	I <sub>AS</sub>	7.5	A
Avalanche Energy, L = 3mH (Note 8)	E <sub>AS</sub>	85	mJ

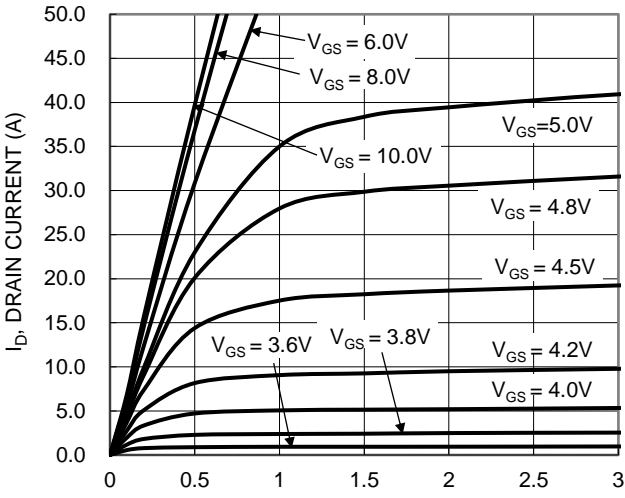
**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	2	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	75	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	3.7	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	40	°C/W
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	2	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

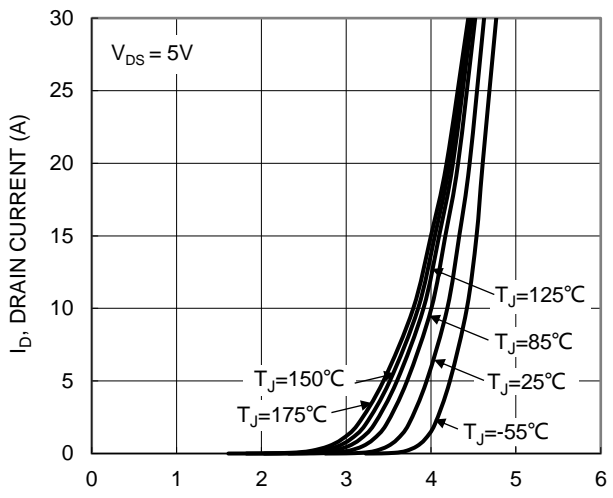
**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	—	4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	11.1	14	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
		—	14.7	20		V <sub>GS</sub> = 6V, I <sub>D</sub> = 20A
Diode Forward Voltage	V <sub>SD</sub>	—	0.86	1.3	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	2343	—	pF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	487	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	26	—		
Gate Resistance	R <sub>g</sub>	—	0.69	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	30.1	—	nC	V <sub>DD</sub> = 50V, I <sub>D</sub> = 10A, V <sub>GS</sub> = 10V
Gate-Source Charge	Q <sub>gs</sub>	—	7.5	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	6.5	—		
Turn-On Delay Time	t <sub>d(ON)</sub>	—	9.8	—	ns	V <sub>DD</sub> = 50V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A, R <sub>g</sub> = 6Ω
Turn-On Rise Time	t <sub>r</sub>	—	7.8	—		
Turn-Off Delay Time	t <sub>d(OFF)</sub>	—	22.5	—		
Turn-Off Fall Time	t <sub>f</sub>	—	9.6	—		
Reverse Recovery Time	t <sub>RR</sub>	—	43	—	ns	I <sub>F</sub> = 10A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	65.1	—	nC	

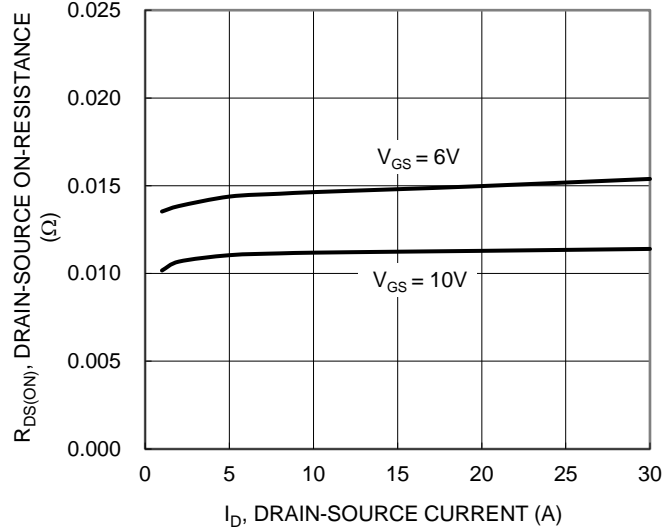
- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.



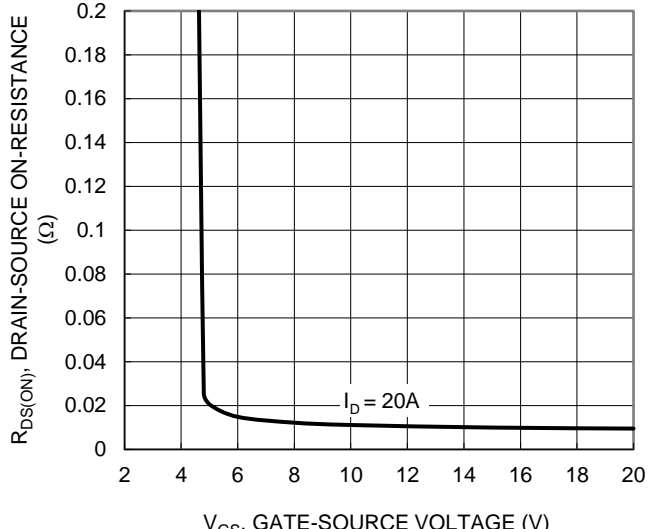
$V_{DS}$ , DRAIN-SOURCE VOLTAGE (V)  
Figure 1. Typical Output Characteristic



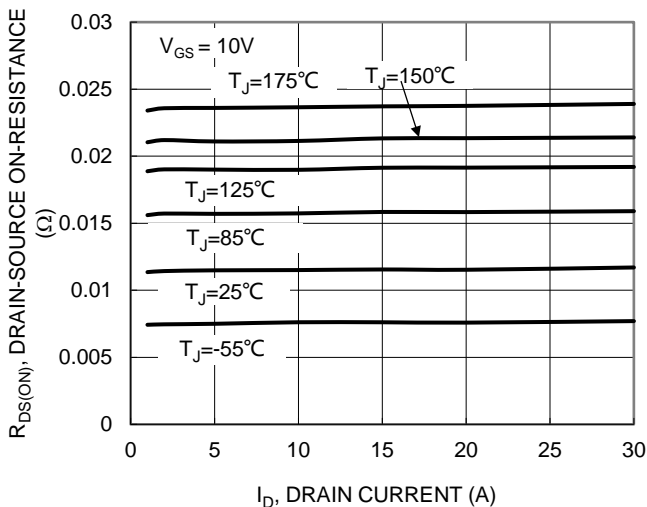
$V_{GS}$ , GATE-SOURCE VOLTAGE (V)  
Figure 2. Typical Transfer Characteristic



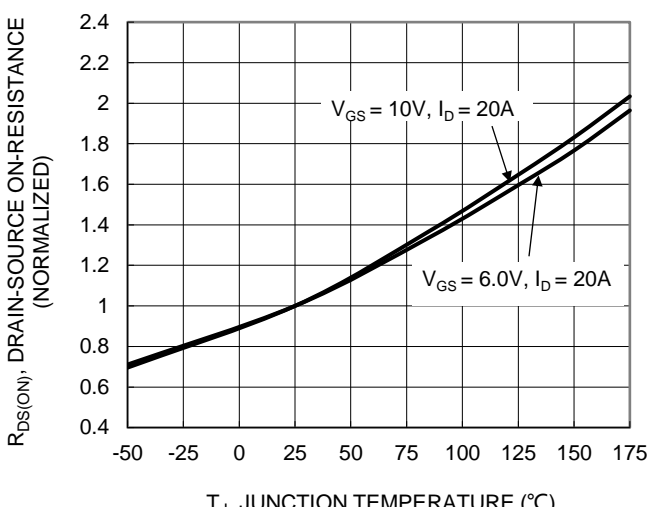
$I_D$ , DRAIN-SOURCE CURRENT (A)  
Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage



$V_{GS}$ , GATE-SOURCE VOLTAGE (V)  
Figure 4. Typical Transfer Characteristic



$I_D$ , DRAIN CURRENT (A)  
Figure 5. Typical On-Resistance vs. Drain Current and Temperature



$T_J$ , JUNCTION TEMPERATURE (°C)  
Figure 6. On-Resistance Variation with Temperature

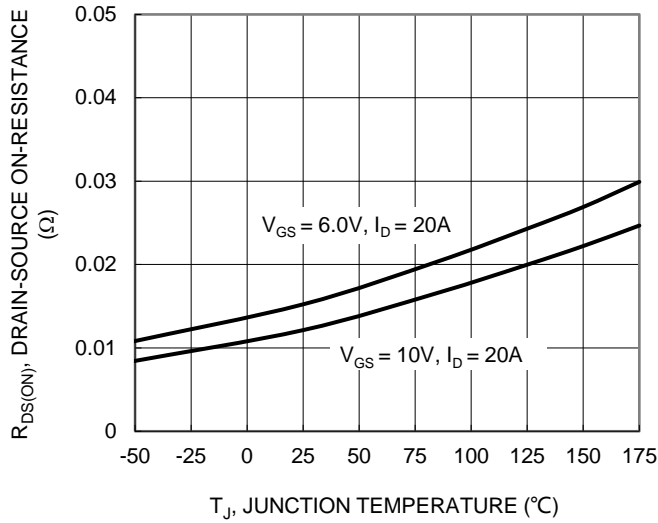


Figure 7. On-Resistance Variation with Temperature

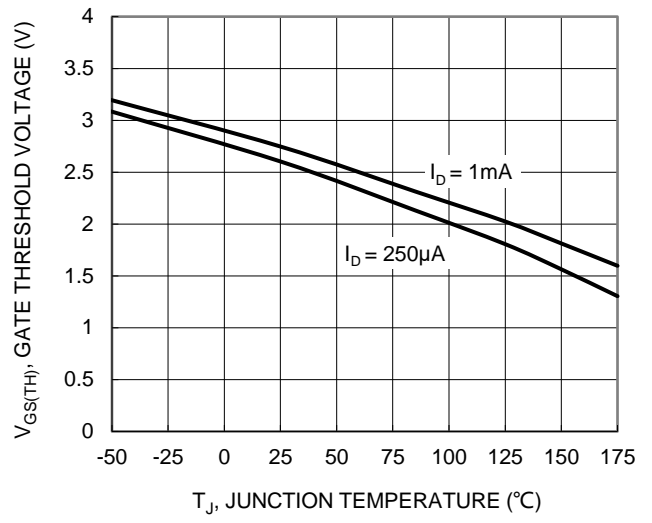


Figure 8. Gate Threshold Variation vs. Junction Temperature

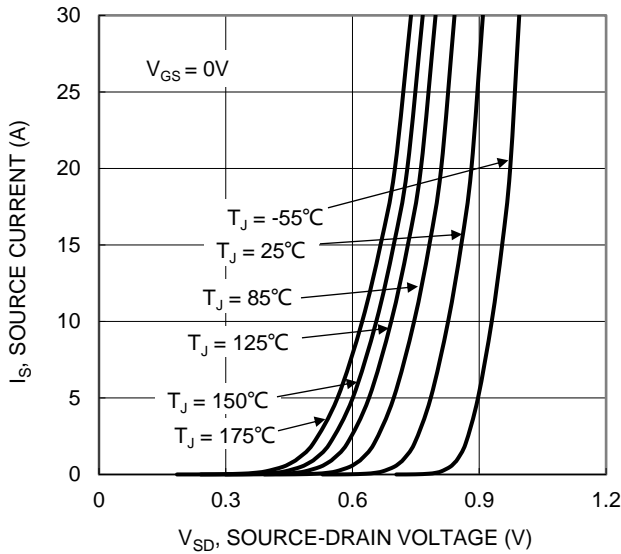


Figure 9. Diode Forward Voltage vs. Current

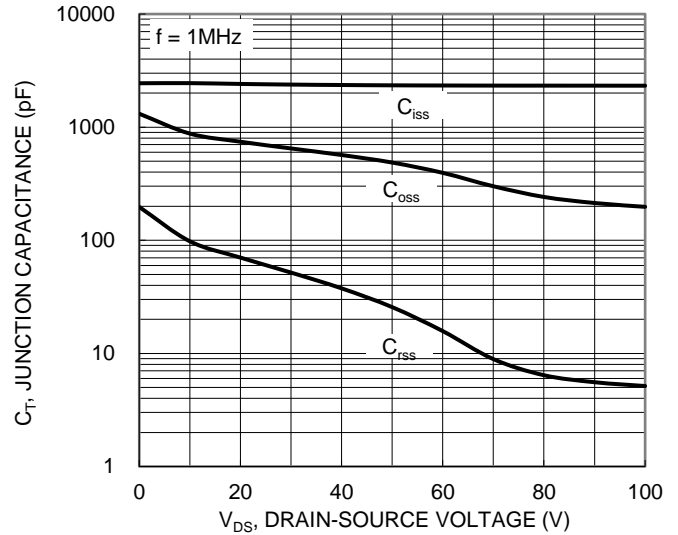


Figure 10. Typical Junction Capacitance

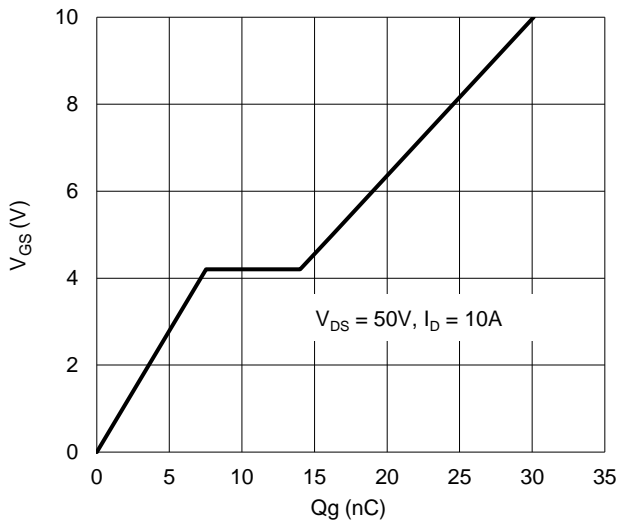


Figure 11. Gate Charge

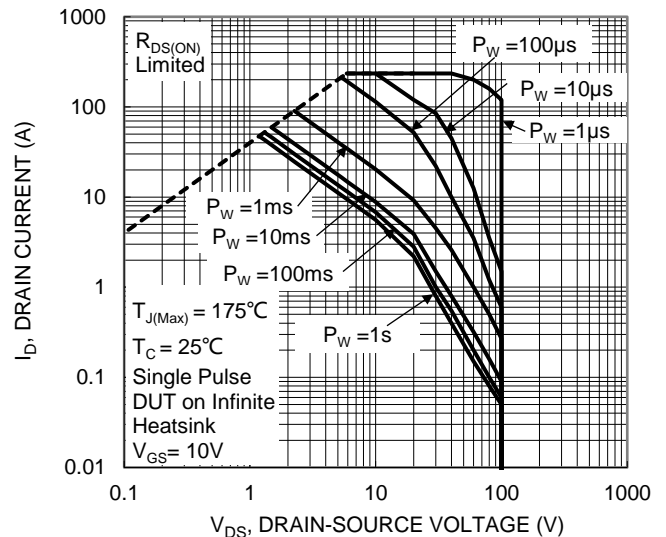


Figure 12. SOA, Safe Operation Area

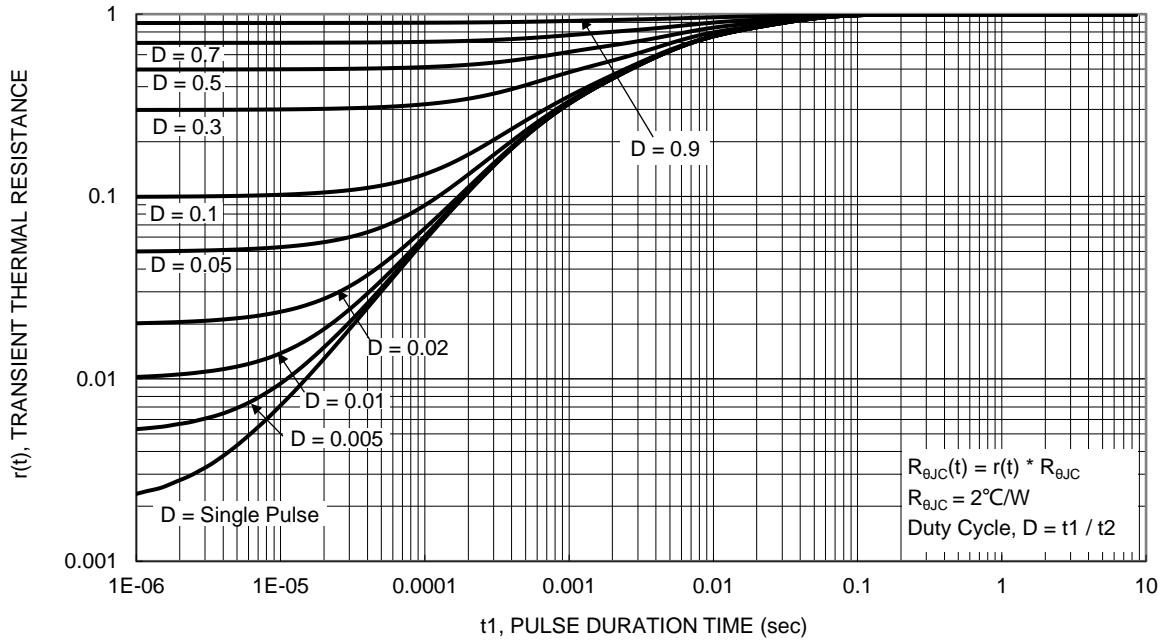
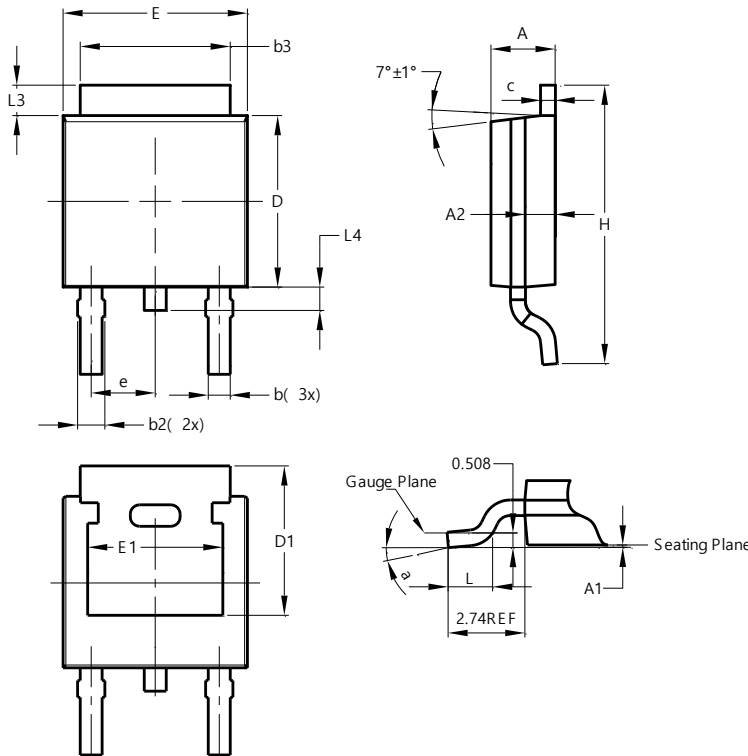


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**TO252 (DPAK)**

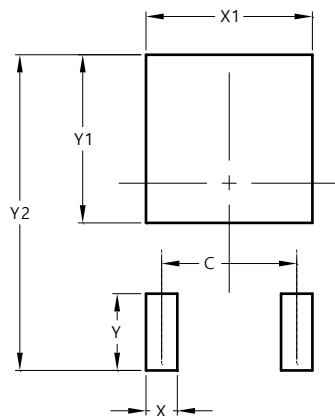


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**TO252 (DPAK)**



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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